

Abstract of the Disclosure:

A semiconductor configuration includes a semiconductor body with a first connection zone of a first conductivity type, a second connection zone of the first conductivity type, a 5 channel zone of the first conductivity type, and at least one control electrode surrounded by an insulation layer. The channel zone is formed between the first connection zone and the second connection zone. The at least one control electrode extends, adjacent to the channel zone, from the first connection zone to the second connection zone. The first connection zone, the second connection zone and the at least one control electrode extend in the vertical direction such that, when a voltage is applied between the first and second connection zones, a current path along the lateral direction is formed in the channel zone.

10  
15  
20  
25  
30  
35  
40  
45  
50  
55  
60  
65  
70  
75  
80  
85  
90  
95

MB/tk